

Supporting Information

# Skin-Compatible Amorphous Oxide Thin-Film-Transistors with a Stress-Released Elastic Architecture

Kyung-Tae Kim <sup>1</sup>, Seung-Han Kang <sup>1</sup>, Seung-Ji Nam <sup>1</sup>, Chan-Yong Park <sup>1</sup>, Jeong-Wan Jo <sup>2</sup>, Jae Sang Heo <sup>3,\*</sup>, and Sung Kyu Park <sup>1,\*</sup>

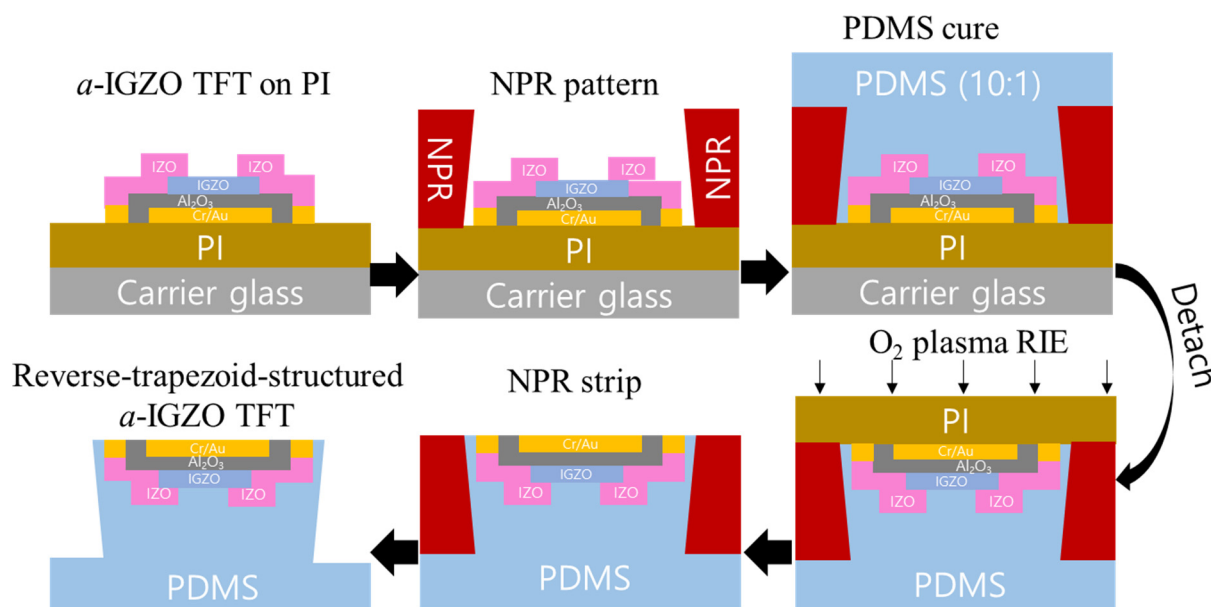
<sup>1</sup> School of Electrical and Electronics Engineering, Chung-Ang University, Seoul 06974, Korea; ktkim0314@gmail.com (K.-T. K.); seunhan\_k@naver.com (S.-H. K.); seungjee@gmail.com (S.-J. N.); mgs01170@gmail.com (C.-Y. P.); skpark@cau.ac.kr (S. K. P.)

<sup>2</sup> Department of Electrical Engineering, University of Cambridge, Cambridge CB2 1TN, UK; jzw0108@gmail.com (J.-W. J.)

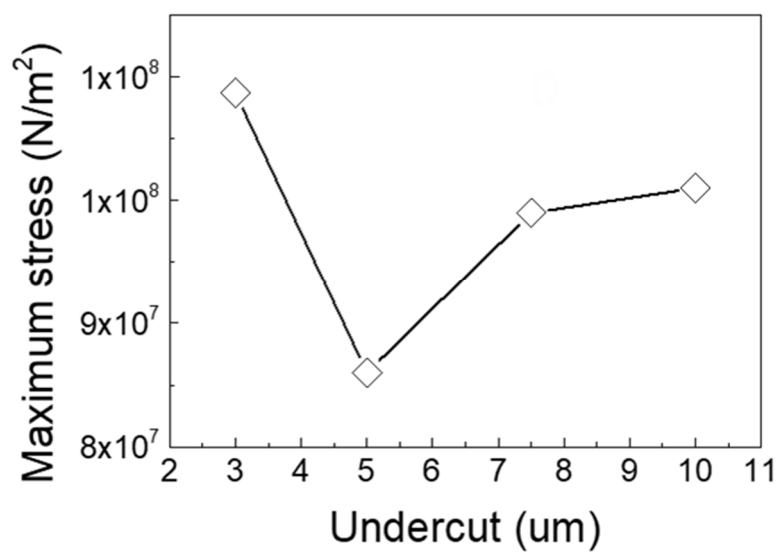
<sup>3</sup> SKKU Advanced Institute of Nanotechnology (SAINT), Sungkyunkwan University, Suwon 16419, Korea; heojs38@gmail.com (J. S. H.)

\* Correspondence: skpark@cau.ac.kr (S. K. P.); heojs38@gmail.com (J. S. H.)

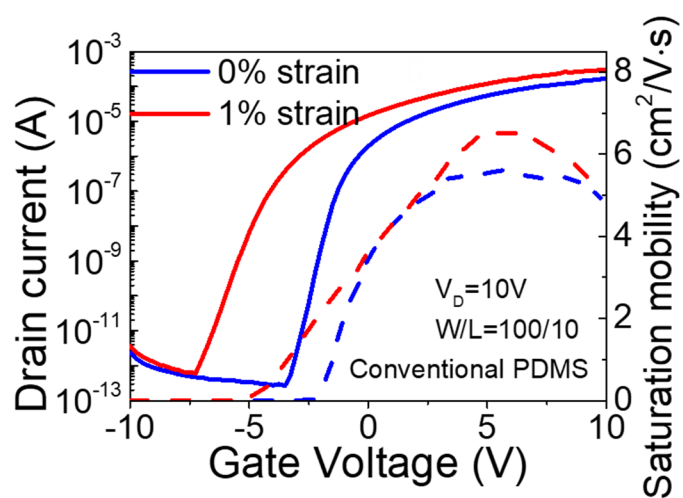
This “Supporting Information” includes: Figure S1 to S3



**Figure S1.** The fabrication steps for reverse-trapezoid-structured *a*-IGZO TFTs



**Figure S2.** The maximum stress induced within a-IGZO TFT devices on reverse-trapezoid substrates with various undercut dimensions



**Figure S3.** Transfer characteristics and saturation mobility of a-IGZO TFTs on conventional PDMS.